

TLP5754H

1. Applications

- Industrial Inverters
- MOSFET Gate Drivers
- IGBT Gate Drivers
- Induction Cooktop and Home Appliances
- Air Conditioner Inverters

2. General

The TLP5754H consists of an infrared LED and an integrated high-gain, high-speed photodetector and is housed in the 6-pin SO6L package.

It provides guaranteed performance and specifications at temperature up to 125 °C.

The TLP5754H is 50 % smaller than the 8-pin DIP package and meets the reinforced insulation class requirements of international standards. Therefore the mounting area can be reduced in equipment requiring the safety standard certification.

The TLP5754H has an internal faraday shield that provides a guaranteed common-mode transient immunity of ± 35 kV/ μ s.

In particular, the TLP5754H has rail to rail output, and this enables stable operation and better switching performance in system.

3. Features

- (1) Buffer logic type (totem pole output)
- (2) Output peak current: ± 4.0 A (max)
- (3) Operating temperature: -40 to 125 °C
- (4) Supply current: 3.0 mA (max)
- (5) Supply voltage: 15 to 30 V
- (6) Threshold input current: 4 mA (max)
- (7) Propagation delay time: 150 ns (max)
- (8) Common-mode transient immunity: ± 35 kV/ μ s (min)
- (9) Isolation voltage: 5000 Vrms (min)
- (10) Safety standards

UL-recognized: UL 1577, File No.E67349

cUL-recognized: CSA Component Acceptance Service No.5A File No.E67349

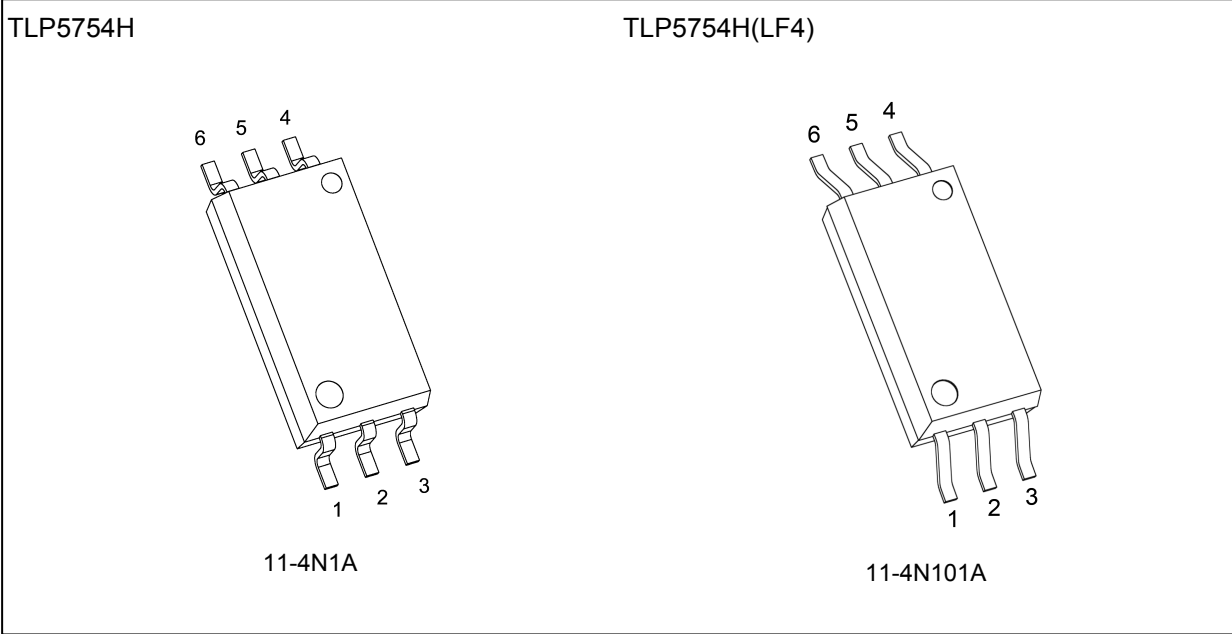
VDE-approved: EN 60747-5-5, EN 62368-1 (**Note 1**)

CQC-approved: GB4943.1, GB8898 Japan Factory

Note 1: When a VDE approved type is needed, please designate the **Option (D4)**.

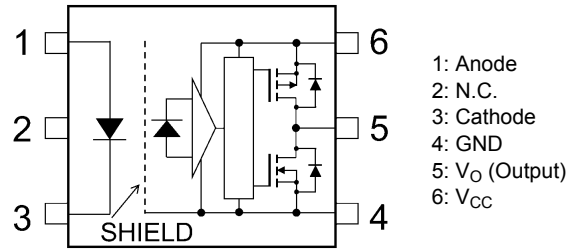
Start of commercial production
2019-06

4. Packaging (Note)

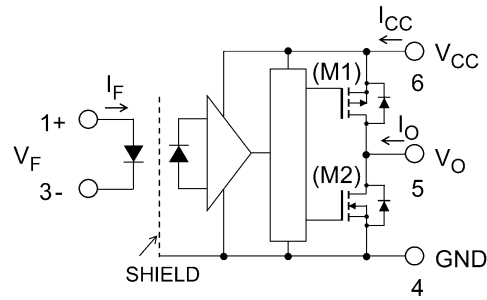


Note: Lead forming option: (LF4)
Taping option: (TP4)

5. Pin Assignment



6. Internal Circuit (Note)



Note: A 1- μ F bypass capacitor must be connected between pin 6 and pin 4.
Note: It is not recommended that a current flow is applied to the body diode at the output stage MOSFET.

7. Principle of Operation

7.1. Truth Table

Input	LED	M1	M2	Output
H	ON	ON	OFF	H
L	OFF	OFF	ON	L

7.2. Mechanical Parameters

Characteristics	Size	Unit
Creepage distances	8.0 (min)	mm
Clearance distances	8.0 (min)	
Internal isolation thickness	0.4 (min)	

8. Absolute Maximum Ratings (Note) (Unless otherwise specified, $T_a = 25\text{ }^{\circ}\text{C}$)

	Characteristics	Symbol	Note	Rating	Unit
LED	Input forward current	I_F		20	mA
	Input forward current derating ($T_a \geq 105\text{ }^{\circ}\text{C}$)	$\Delta I_F / \Delta T_a$		-0.45	mA/ $^{\circ}\text{C}$
	Peak transient input forward current	I_{FPT}	(Note 1)	1	A
	Peak transient input forward current derating ($T_a \geq 85\text{ }^{\circ}\text{C}$)	$\Delta I_{FPT} / \Delta T_a$		-15.4	mA/ $^{\circ}\text{C}$
	Input reverse voltage	V_R		5	V
	Input power dissipation	P_D		40	mW
	Input power dissipation derating ($T_a \geq 85\text{ }^{\circ}\text{C}$)	$\Delta P_D / \Delta T_a$		-0.62	mW/ $^{\circ}\text{C}$
	Junction temperature	T_j		150	$^{\circ}\text{C}$
Detector	Peak high-level output current ($T_a = -40\text{ to }125\text{ }^{\circ}\text{C}$)	I_{OPH}	(Note 2)	-4.0	A
	Peak low-level output current ($T_a = -40\text{ to }125\text{ }^{\circ}\text{C}$)	I_{OPL}	(Note 2)	+4.0	A
	Output voltage	V_O		35	V
	Supply voltage	V_{CC}		35	V
	Output power dissipation	P_O		810	mW
	Output power dissipation derating ($T_a \geq 85\text{ }^{\circ}\text{C}$)	$\Delta P_O / \Delta T_a$		-12.5	mW/ $^{\circ}\text{C}$
	Junction temperature	T_j		150	$^{\circ}\text{C}$
Common	Operating temperature	T_{opr}		-40 to 125	$^{\circ}\text{C}$
	Storage temperature	T_{stg}		-55 to 150	$^{\circ}\text{C}$
	Lead soldering temperature (10 s)	T_{sol}	(Note 3)	260	$^{\circ}\text{C}$
	Isolation voltage AC, 60 s, R.H. $\leq 60\%$	BV_S	(Note 4)	5000	Vrms

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

Note 1: Pulse width (PW) $\leq 1\text{ }\mu\text{s}$, 300 pps

Note 2: Exponential waveform. Pulse width $\leq 2\text{ }\mu\text{s}$, $f \leq 15\text{ kHz}$

Note 3: $\geq 2\text{ mm}$ below seating plane.

Note 4: This device is considered as a two-terminal device: Pins 1, 2 and 3 are shorted together, and pins 4, 5 and 6 are shorted together.

9. Recommended Operating Conditions (Note)

Characteristics	Symbol	Note	Min	Typ.	Max	Unit
Input on-state current	$I_{F(ON)}$	(Note 1)	6	—	11	mA
Input off-state voltage	$V_{F(OFF)}$		0	—	0.8	V
Supply voltage	V_{CC}	(Note 2)	15	—	30	
Peak high-level output current	I_{OPH}		—	—	-4.0	A
Peak low-level output current	I_{OPL}		—	—	+4.0	
Operating frequency	f	(Note 3)	—	—	50	kHz

Note: The recommended operating conditions are given as a design guide necessary to obtain the intended performance of the device. Each parameter is an independent value. When creating a system design using this device, the electrical characteristics specified in this data sheet should also be considered.

Note: A ceramic capacitor (1 μ F) should be connected between pin 6 (V_{CC}) and pin 4 (GND) to stabilize the operation of a high-gain linear amplifier. Otherwise, this photocoupler may not switch properly. The bypass capacitor should be placed within 1 cm of each pin.

Note 1: The rise and fall times of the input on-current should be less than 0.5 μ s.

Note 2: Denotes the operating range, not the recommended operating condition.

Note 3: Exponential waveform. $I_{OPH} \geq -4.0$ A (≤ 90 ns), $I_{OPL} \leq 4.0$ A (≤ 90 ns), $T_a = 125$ °C

10. Electrical Characteristics (Note) (Unless otherwise specified, $T_a = -40$ to 125 °C)

Characteristics	Symbol	Note	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Input forward voltage	V_F			$I_F = 10$ mA, $T_a = 25$ °C	1.45	1.55	1.70	V
Input forward voltage temperature coefficient	$\Delta V_F / \Delta T_a$			$I_F = 10$ mA	—	-1.8	—	mV/°C
Input reverse current	I_R			$V_R = 5$ V, $T_a = 25$ °C	—	—	10	μ A
Input capacitance	C_t			$V = 0$ V, $f = 1$ MHz, $T_a = 25$ °C	—	60	—	pF
Peak high-level output current	I_{OPH}	(Note 1)	Fig. 13.1.1	$I_F = 5$ mA, $V_{CC} = 30$ V, $V_{6-5} = -3.5$ V	—	—	-1.2	A
				$I_F = 5$ mA, $V_{CC} = 15$ V, $V_{6-5} = -7$ V	—	—	-2.9	
Peak low-level output current	I_{OPL}	(Note 1)	Fig. 13.1.2	$I_F = 0$ mA, $V_{CC} = 30$ V, $V_{5-4} = 2.5$ V	1.2	—	—	
				$I_F = 0$ mA, $V_{CC} = 15$ V, $V_{5-4} = 7$ V	2.9	—	—	
High-level output voltage	V_{OH}		Fig. 13.1.3	$I_F = 4$ mA, $V_{CC} = 15$ V, $I_O = -100$ mA	14.7	14.9	—	V
Low-level output voltage	V_{OL}		Fig. 13.1.4	$V_F = 0.8$ V, $V_{CC} = 15$ V, $I_O = 100$ mA	—	0.07	0.2	
High-level supply current	I_{CCH}		Fig. 13.1.5	$I_F = 10$ mA, $V_{CC} = 30$ V, $V_O = \text{Open}$	—	1.8	3.0	mA
Low-level supply current	I_{CCL}		Fig. 13.1.6	$I_F = 0$ mA, $V_{CC} = 30$ V, $V_O = \text{Open}$	—	1.7	3.0	
Threshold input current (L/H)	I_{FLH}			$V_{CC} = 15$ V, $V_O > 1$ V	—	1.4	4	
Threshold input voltage (H/L)	V_{FHL}			$V_{CC} = 15$ V, $V_O < 1$ V	0.8	—	—	V
Supply voltage	V_{CC}			—	15	—	30	
UVLO threshold voltage	V_{UVLO+}			$I_F = 5$ mA, $V_O > 2.5$ V	12.1	12.7	13.5	
	V_{UVLO-}			$I_F = 5$ mA, $V_O < 2.5$ V	11.1	11.7	12.4	
UVLO hysteresis	$UVLO_{HYS}$			—	—	1.0	—	

Note: All typical values are at $T_a = 25$ °C.

Note 1: I_O application time ≤ 50 μ s; single pulse.

11. Isolation Characteristics (Unless otherwise specified, $T_a = 25\text{ }^{\circ}\text{C}$)

Characteristics	Symbol	Note	Test Condition	Min	Typ.	Max	Unit
Total capacitance (input to output)	C_S	(Note 1)	$V_S = 0\text{ V}$, $f = 1\text{ MHz}$	—	1.0	—	pF
Isolation resistance	R_S	(Note 1)	$V_S = 500\text{ V}$, R.H. $\leq 60\%$	10^{12}	10^{14}	—	Ω
Isolation voltage	BV_S	(Note 1)	AC, 60 s	5000	—	—	Vrms

Note 1: This device is considered as a two-terminal device: Pins 1, 2 and 3 are shorted together, and pins 4, 5 and 6 are shorted together.

12. Switching Characteristics (Note) (Unless otherwise specified, $T_a = -40\text{ to }125\text{ }^{\circ}\text{C}$)

Characteristics	Symbol	Note	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Propagation delay time (L/H)	t_{pLH}	(Note 1)	Fig. 13.1.7	$I_F = 0 \rightarrow 10\text{ mA}$, $V_{CC} = 30\text{ V}$, $R_g = 10\text{ }\Omega$, $C_g = 25\text{ nF}$	50	—	150	ns
Propagation delay time (H/L)	t_{pHL}	(Note 1)	Fig. 13.1.7	$I_F = 10 \rightarrow 0\text{ mA}$, $V_{CC} = 30\text{ V}$, $R_g = 10\text{ }\Omega$, $C_g = 25\text{ nF}$	50	—	150	ns
Rise time	t_r	(Note 1)	Fig. 13.1.7	$I_F = 0 \rightarrow 10\text{ mA}$, $V_{CC} = 30\text{ V}$, $R_g = 10\text{ }\Omega$, $C_g = 25\text{ nF}$	—	15	—	ns
Fall time	t_f	(Note 1)	Fig. 13.1.7	$I_F = 10 \rightarrow 0\text{ mA}$, $V_{CC} = 30\text{ V}$, $R_g = 10\text{ }\Omega$, $C_g = 25\text{ nF}$	—	8	—	ns
Pulse width distortion	$ t_{pHL} - t_{pLH} $	(Note 1)	Fig. 13.1.7	$I_F = 0 \leftrightarrow 10\text{ mA}$, $V_{CC} = 30\text{ V}$, $R_g = 10\text{ }\Omega$, $C_g = 25\text{ nF}$	—	—	50	ns
Propagation delay skew (device to device)	t_{psk}	(Note 1), (Note 2)	Fig. 13.1.7	$I_F = 0 \leftrightarrow 10\text{ mA}$, $V_{CC} = 30\text{ V}$, $R_g = 10\text{ }\Omega$, $C_g = 25\text{ nF}$	-80	—	80	ns
High-level common-mode transient immunity	CM_H	(Note 3)	Fig. 13.1.8	$V_{CM} = 1000\text{ V}_{p-p}$, $I_F = 5\text{ mA}$, $V_{CC} = 30\text{ V}$, $T_a = 25\text{ }^{\circ}\text{C}$, $V_{O(min)} = 26\text{ V}$	± 35	—	—	kV/ μs
Low-level common-mode transient immunity	CM_L	(Note 4)		$V_{CM} = 1000\text{ V}_{p-p}$, $I_F = 0\text{ mA}$, $V_{CC} = 30\text{ V}$, $T_a = 25\text{ }^{\circ}\text{C}$, $V_{O(max)} = 1\text{ V}$	± 35	—	—	kV/ μs

Note: All typical values are at $T_a = 25\text{ }^{\circ}\text{C}$.

Note 1: $f = 25\text{ kHz}$, duty = 50 %, input current $t_r = t_f = 5\text{ ns}$ or less

Note 2: The propagation delay skew, t_{psk} , is equal to the magnitude of the worst-case difference in t_{pHL} and/or t_{pLH} that will be seen between units at the same given conditions (supply voltage, input current, temperature, etc).

Note 3: CM_H is the maximum rate of fall of the common mode voltage that can be sustained with the output voltage in the logic high state ($V_O > 26\text{ V}$).

Note 4: CM_L is the maximum rate of rise of the common mode voltage that can be sustained with the output voltage in the logic low state ($V_O < 1\text{ V}$).

13. Test Circuits and Characteristics Curves

13.1. Test Circuits

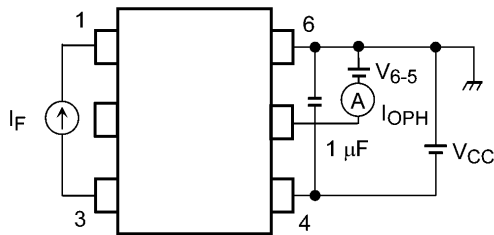


Fig. 13.1.1 I_{OPH} Test Circuit

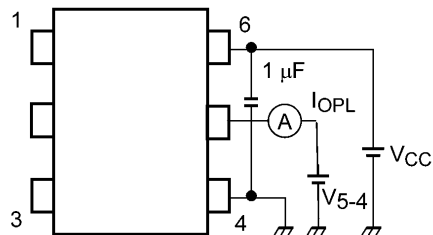


Fig. 13.1.2 I_{OPL} Test Circuit

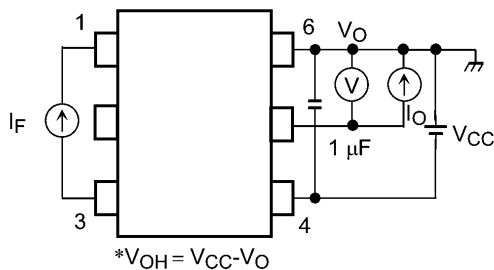


Fig. 13.1.3 V_{OH} Test Circuit

*V_{OH} = V_{CC} - V_O

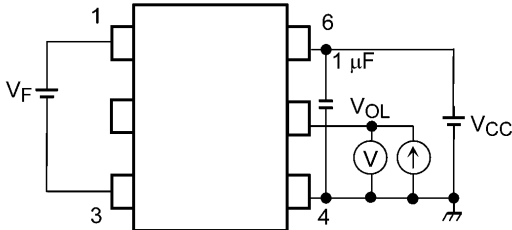


Fig. 13.1.4 V_{OL} Test Circuit

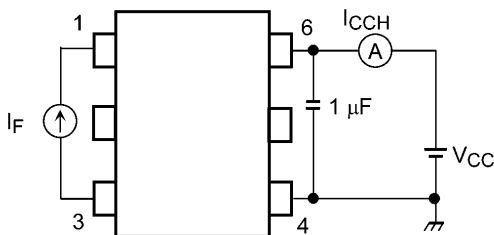


Fig. 13.1.5 I_{CCH} Test Circuit

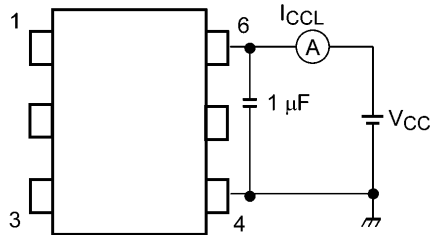


Fig. 13.1.6 I_{CCL} Test Circuit

I_F = 10 mA (P.G.)
(f = 25 kHz, duty = 50 %, t_r = t_f = 5 ns or less)

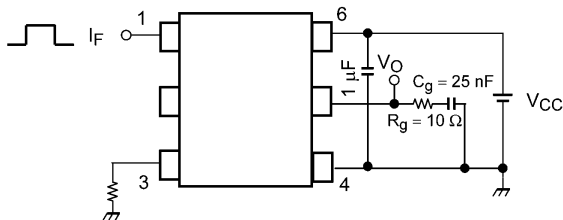


Fig. 13.1.7 Switching Time Test Circuit and Waveform

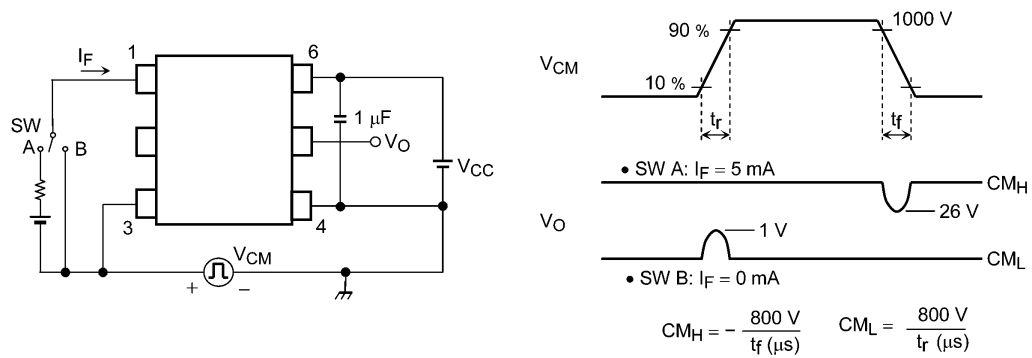


Fig. 13.1.8 Common-Mode Transient Immunity Test Circuit and Waveform

13.2. Characteristics Curves (Note)

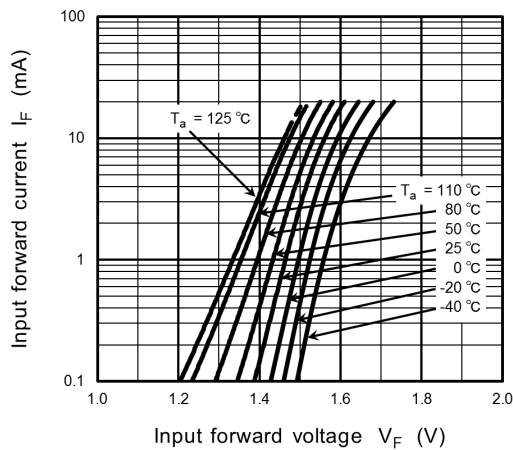


Fig. 13.2.1 $I_F - V_F$

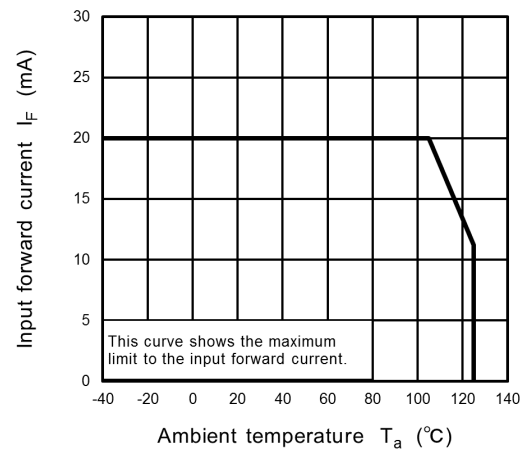


Fig. 13.2.2 $I_F - T_a$

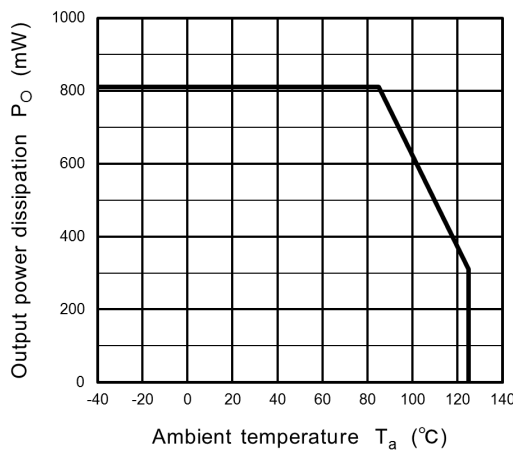


Fig. 13.2.3 $P_O - T_a$

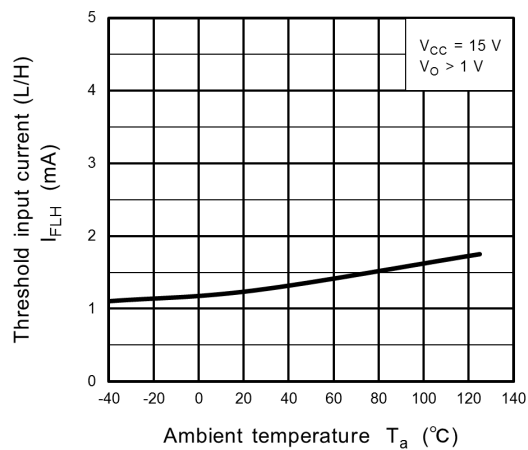


Fig. 13.2.4 $I_{FLH} - T_a$

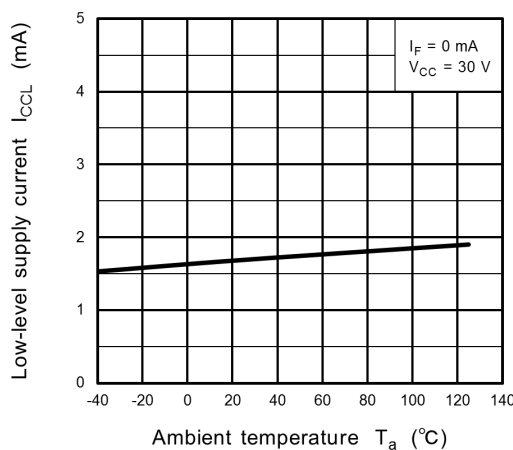


Fig. 13.2.5 $I_{CCL} - T_a$

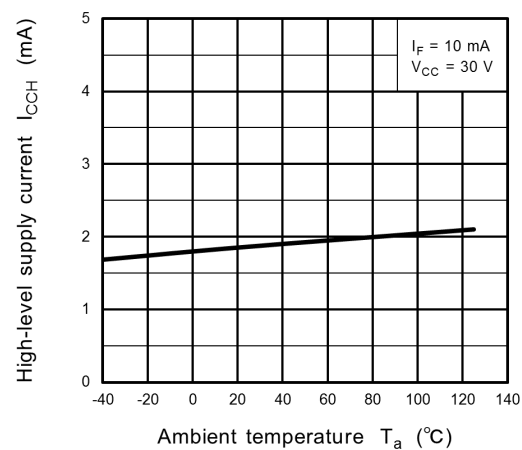


Fig. 13.2.6 $I_{CCH} - T_a$

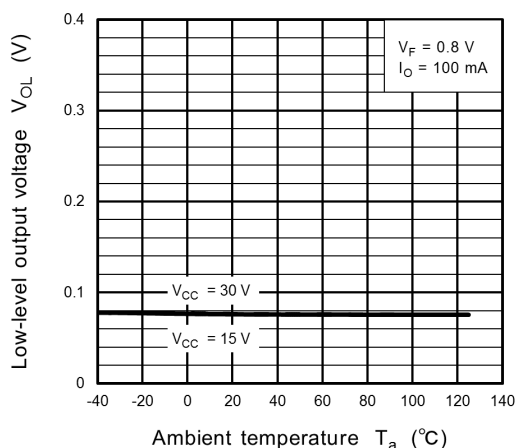


Fig. 13.2.7 $V_{OL} - T_a$

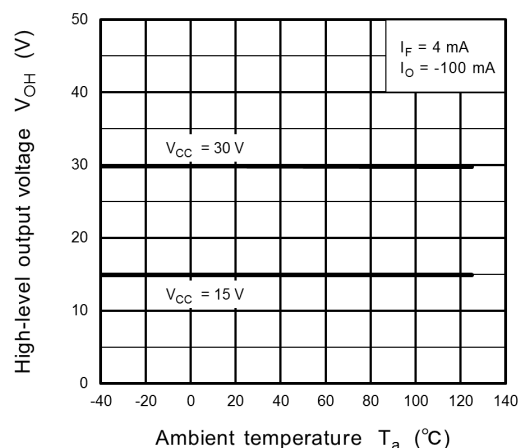


Fig. 13.2.8 $V_{OH} - T_a$

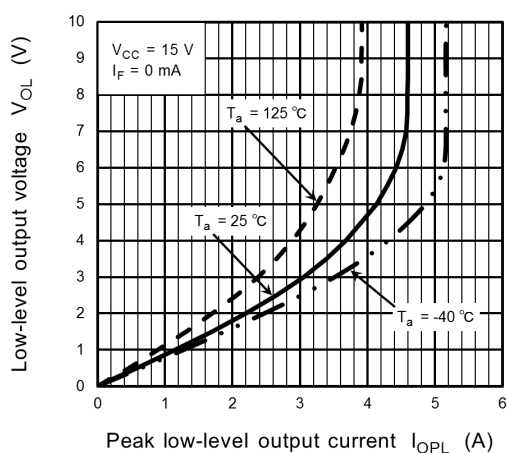


Fig. 13.2.9 $V_{OL} - I_{OPL}$

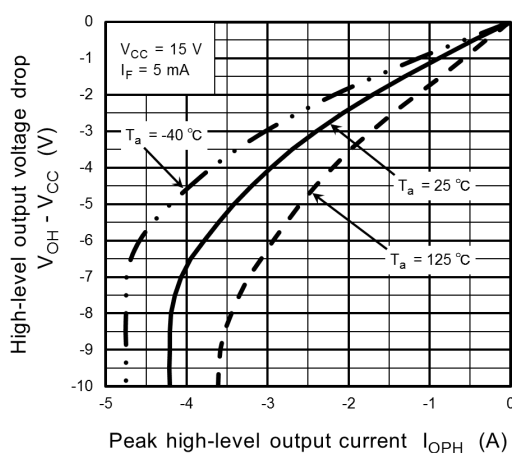


Fig. 13.2.10 $(V_{OH} - V_{CC}) - I_{OPH}$

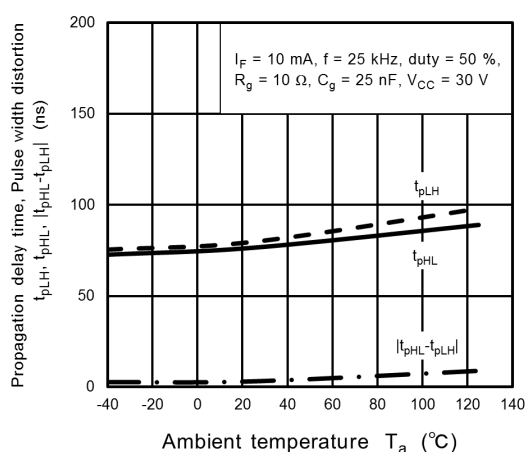


Fig. 13.2.11 t_{PLH} , t_{PHL} , $|t_{PHL} - t_{PLH}| - T_a$

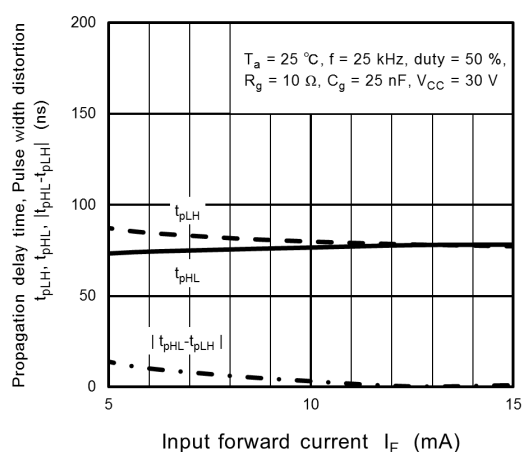


Fig. 13.2.12 t_{PLH} , t_{PHL} , $|t_{PHL} - t_{PLH}| - I_F$

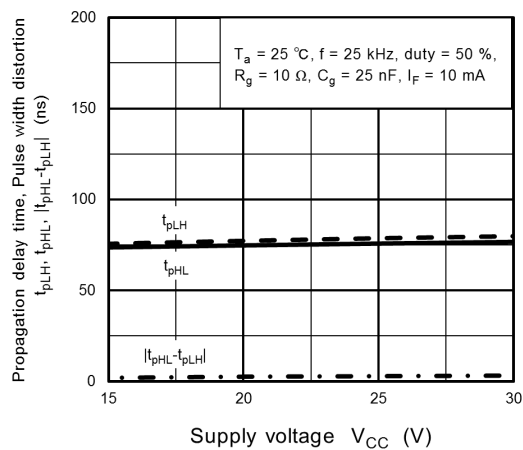


Fig. 13.2.13 t_{PLH} , t_{PHL} , $|t_{PHL} - t_{PLH}| - V_{CC}$

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

14. Soldering and Storage

14.1. Precautions for Soldering

The soldering temperature should be controlled as closely as possible to the conditions shown below, irrespective of whether a soldering iron or a reflow soldering method is used.

- When using soldering reflow.

The soldering temperature profile is based on the package surface temperature.
(See the figure shown below, which is based on the package surface temperature.)
Reflow soldering must be performed once or twice.
The mounting should be completed with the interval from the first to the last mountings being 2 weeks.

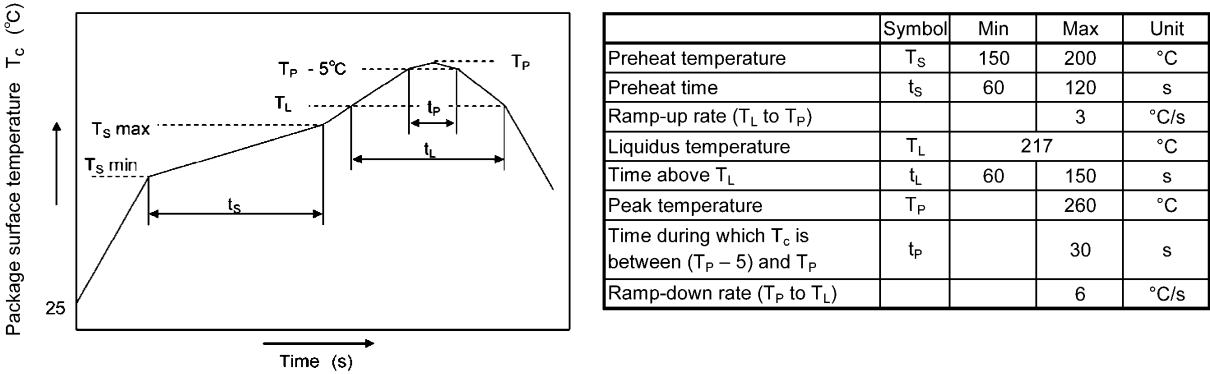


Fig. 14.1.1 An Example of a Temperature Profile When Lead(Pb)-Free Solder Is Used

- When using soldering flow
Preheat the device at a temperature of 150 °C (package surface temperature) for 60 to 120 seconds.
Mounting condition of 260 °C within 10 seconds is recommended.
Flow soldering must be performed once.
- When using soldering Iron
Complete soldering within 10 seconds for lead temperature not exceeding 260 °C or within 3 seconds not exceeding 350 °C
Heating by soldering iron must be done only once per lead.

14.2. Precautions for General Storage

- Avoid storage locations where devices may be exposed to moisture or direct sunlight.
- Follow the precautions printed on the packing label of the device for transportation and storage.
- Keep the storage location temperature and humidity within a range of 5 °C to 35 °C and 45 % to 75 %, respectively.
- Do not store the products in locations with poisonous gases (especially corrosive gases) or in dusty conditions.
- Store the products in locations with minimal temperature fluctuations. Rapid temperature changes during storage can cause condensation, resulting in lead oxidation or corrosion, which will deteriorate the solderability of the leads.
- When restoring devices after removal from their packing, use anti-static containers.
- Do not allow loads to be applied directly to devices while they are in storage.
- If devices have been stored for more than two years under normal storage conditions, it is recommended that you check the leads for ease of soldering prior to use.

15. Land Pattern Dimensions (for reference only)

Unit: mm

TLP5754H

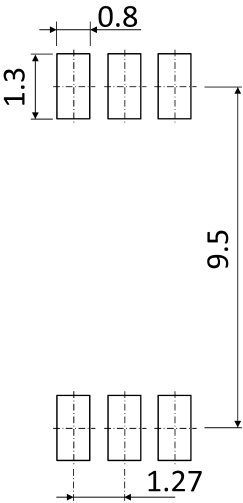


Fig. 15.1 Lead Forming Option (standard)

TLP5754H(LF4)

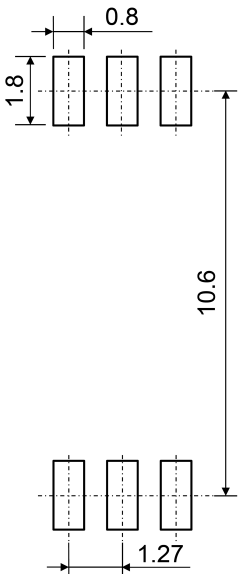
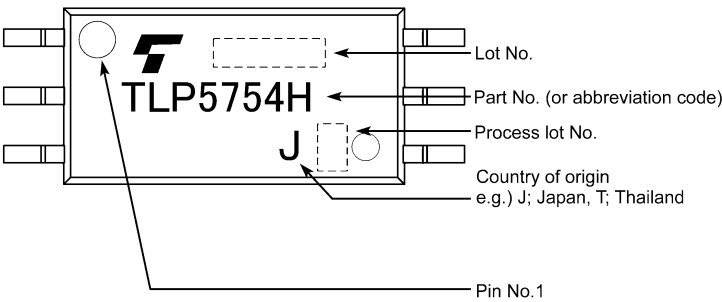


Fig. 15.2 Lead forming and taping option (LF4), (TP4)

16. Marking (Note)



Note: A different marking is used for photocouplers that have been qualified according to option (D4) of EN 60747. See Fig.17.3.

17. EN 60747-5-5 Option (D4) Specification

- Part number: TLP5754H (Note 1)
- The following part naming conventions are used for the devices that have been qualified according to option (D4) of EN 60747.

Example: TLP5754H(D4TP4,E

D4: EN 60747 option

TP4: Tape type

E: [[G]]/RoHS COMPATIBLE (Note 2)

Note 1: Use TOSHIBA standard type number for safety standard application.

e.g., TLP5754H(D4TP4,E → TLP5754H

Note 2: Please contact your Toshiba sales representative for details on environmental information such as the product's RoHS compatibility.

RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

Description	Symbol	Rating	Unit
Application classification			—
for rated mains voltage ≤ 600 Vrms		I-IV	
for rated mains voltage ≤ 1000 Vrms		I-III	
Climatic classification		40 / 125 / 21	—
Pollution degree		2	—
Maximum operating insulation voltage	VIORM	1230	Vpeak
Input to output test voltage, Method A $V_{pr} = 1.6 \times VIORM$, type and sample test $t_p = 10$ s, partial discharge < 5 pC	Vpr	1970	Vpeak
Input to output test voltage, Method B $V_{pr} = 1.875 \times VIORM$, 100 % production test $t_p = 1$ s, partial discharge < 5 pC	Vpr	2310	Vpeak
Highest permissible overvoltage (transient overvoltage, $t_{pr} = 60$ s)	VTR	8000	Vpeak
Safety limiting values (max. permissible ratings in case of fault, also refer to thermal derating curve)			
current (input current I_F , $P_{so} = 0$)	Isi	300	mA
power (output or total power dissipation)	Pso	810	mW
temperature	Ts	150	°C
Insulation resistance			
$V_{IO} = 500$ V, $T_a = 25$ °C	Rsi	$\geq 10^{12}$	Ω
$V_{IO} = 500$ V, $T_a = 100$ °C		$\geq 10^{11}$	
$V_{IO} = 500$ V, $T_a = T_s$		$\geq 10^9$	

Fig. 17.1 EN 60747 Insulation Characteristics

Table Insulation Related Specifications (Note)

Insulation Related Parameters	Symbol	TLP5754H
Minimum creepage distance	Cr	8.0 mm
Minimum clearance	Cl	8.0 mm
Minimum insulation thickness	ti	0.4 mm
Comparative tracking index	CTI	500

Note: This photocoupler is suitable for **safe electrical isolation** only within the safety limit data.
 Maintenance of the safety data shall be ensured by means of protective circuits.



Fig. 17.2 Marking on Packing for EN 60747

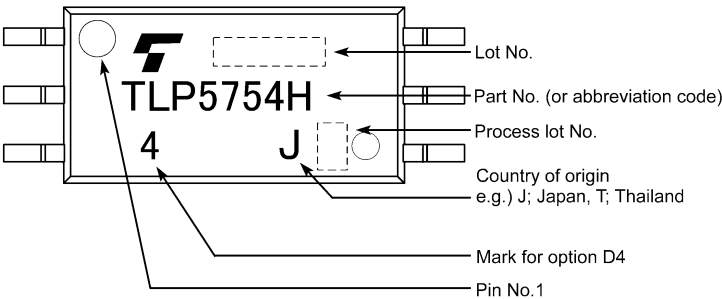
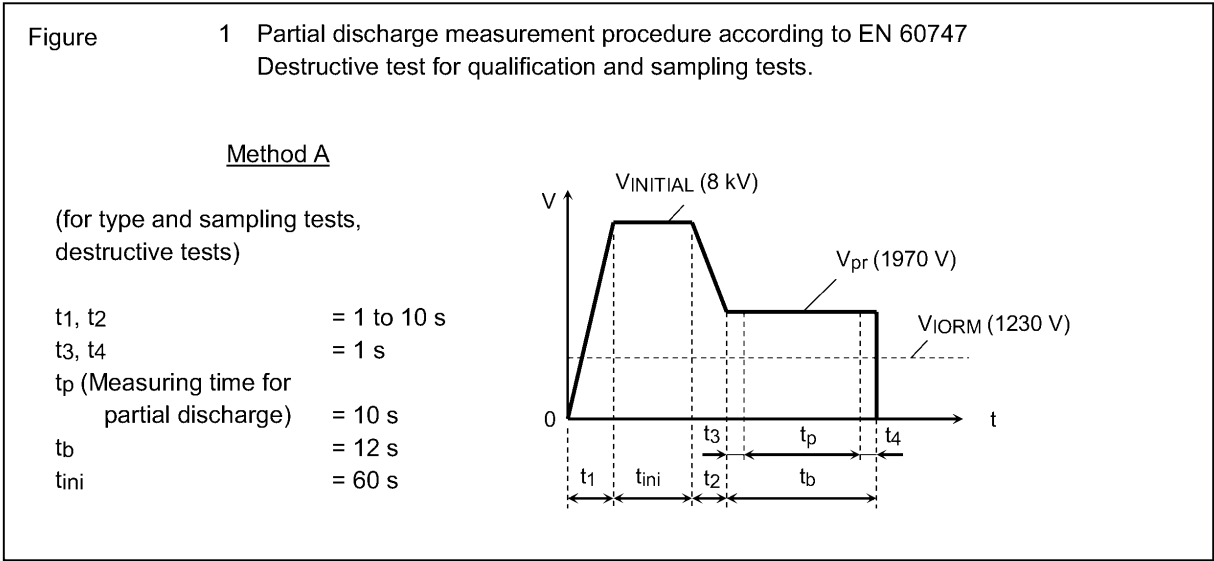


Fig. 17.3 Marking Example (Note)

Note: The above marking is applied to the photocouplers that have been qualified according to option (D4) of EN 60747.

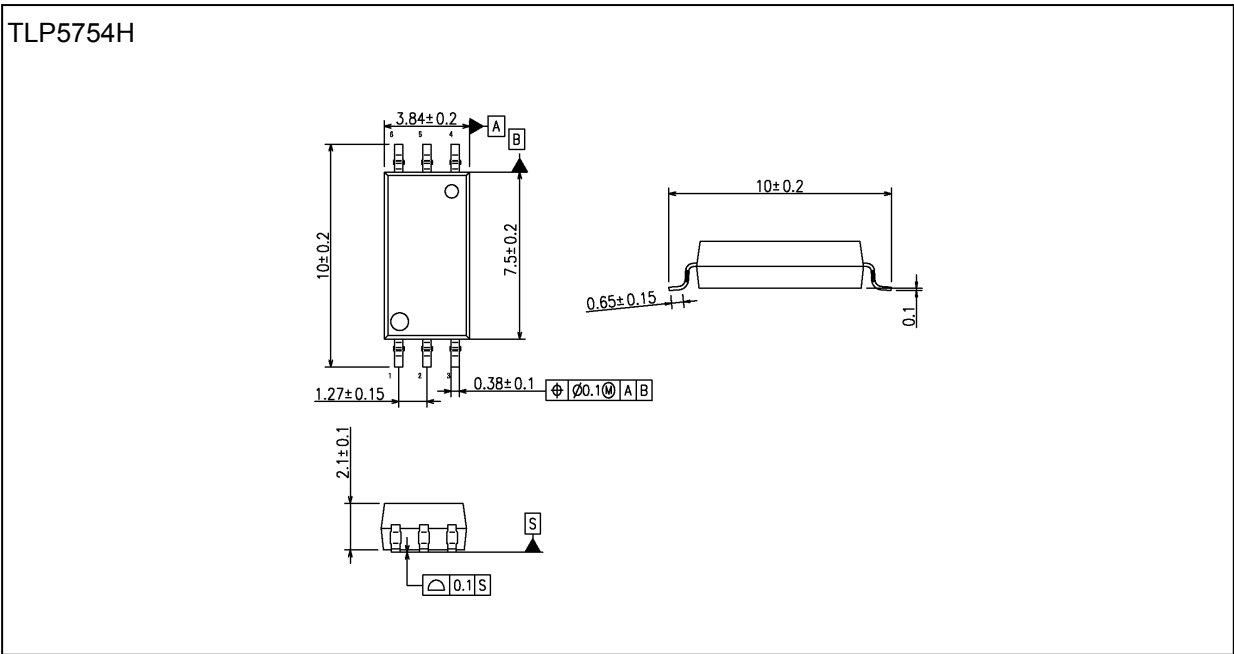


18. Ordering Information (Example of Item Name)

Item Name	Packaging	VDE Option	Packing (MOQ)
TLP5754H(E			Magazine (125 pcs)
TLP5754H(TP,E			Tape and reel (1500 pcs)
TLP5754H(D4,E		EN 60747-5-5	Magazine (125 pcs)
TLP5754H(D4-TP,E		EN 60747-5-5	Tape and reel (1500 pcs)
TLP5754H(LF4,E	LF4, Wide forming		Magazine (125 pcs)
TLP5754H(TP4,E	LF4, Wide forming		Tape and reel (1500 pcs)
TLP5754H(D4LF4,E	LF4, Wide forming	EN 60747-5-5	Magazine (125 pcs)
TLP5754H(D4TP4,E	LF4, Wide forming	EN 60747-5-5	Tape and reel (1500 pcs)

Package Dimensions

Unit: mm

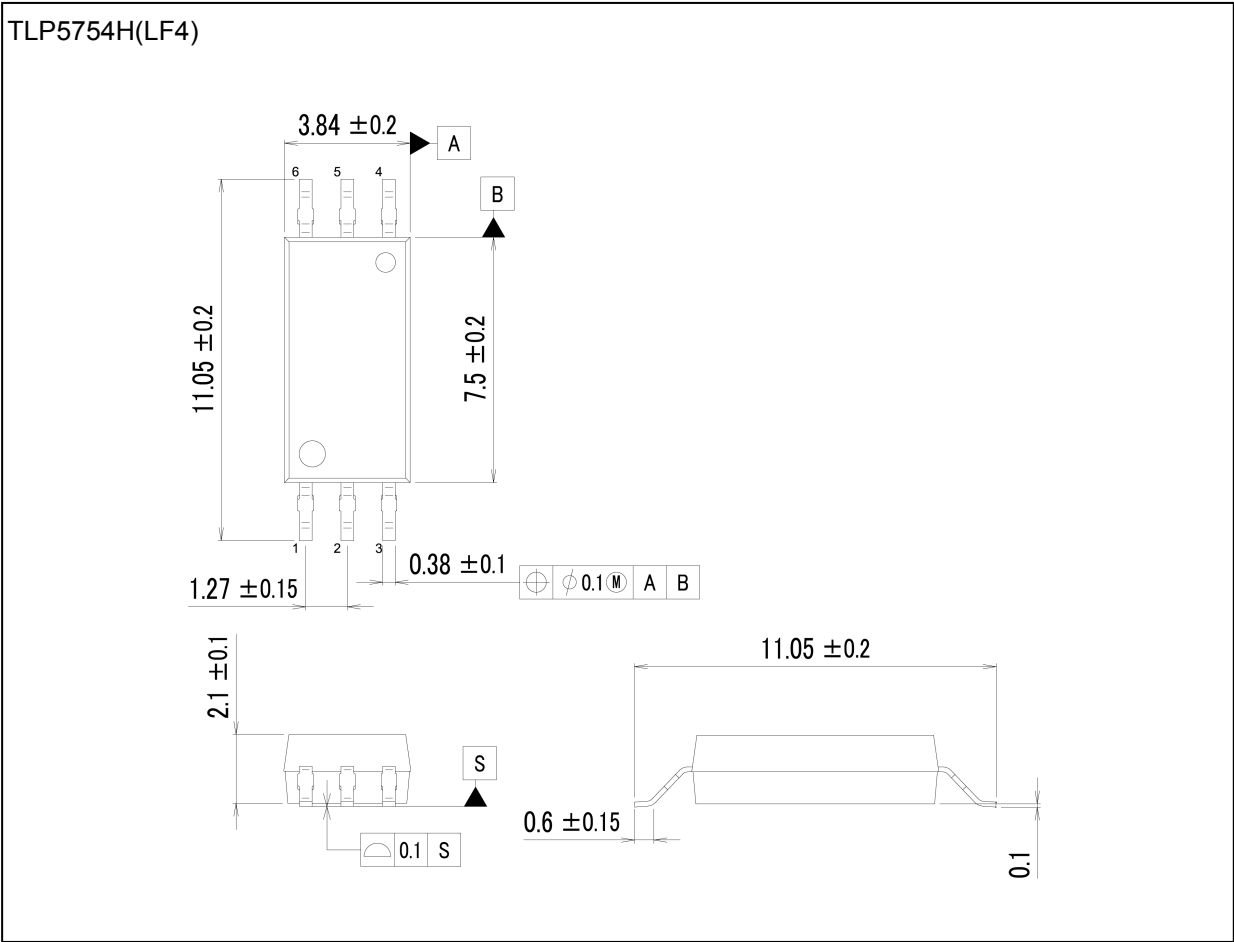


Weight: 0.126 g (typ.)

Package Name(s)
TOSHIBA: 11-4N1A

Package Dimensions

Unit: mm



Weight: 0.126 g (typ.)

Package Name(s)
TOSHIBA: 11-4N101A

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